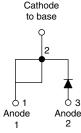
Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 8 A





TO-247AC modified

PRODUCT SUMMARY									
Package	TO-247AC modified (2 pins)								
I _{F(AV)}	8 A								
V _R	1200 V								
V _F at I _F	3.3 V								
t _{rr} (typ.)	28 ns								
T _J max.	150 °C								
Diode variation	Single die								

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA08PB120PbF is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the VS-HFA08PB120PbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08PB120PbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V _R		1200	V					
Maximum continuous forward current	I _F	T _C = 100 °C	8						
Single pulse forward current	I _{FSM}		130	А					
Maximum repetitive forward current	I _{FRM}		32						
Maximum newer dissinction	р	T _C = 25 °C	73.5	W					
Maximum power dissipation	P _D	T _C = 100 °C	29	vv					
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C					

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Pb-free e3

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		1200	-	-			
Maximum forward voltage		I _F = 8.0 A		-	2.6	3.3	v		
	V _{FM}	I _F = 16 A	See fig. 1	-	3.4	4.3			
		I _F = 8.0 A, T _J = 125 °C		-	2.4	3.1			
Maximum reverse	1	$V_{R} = V_{R}$ rated	See fig. 2	-	0.31	10	μA		
leakage current	I _{RM}	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See lig. 2	-	135	1000			
Junction capacitance C _T		V _R = 200 V	See fig. 3	-	11	20	pF		
Series inductance	L _S	Measured lead to lead 5 mm from body	-	8.0	-	nH			

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time See fig. 5, 10	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	0 Α/μs, V _R = 30 V	-	28	-	ns		
	t _{rr1}	T _J = 25 °C		-	63	95			
	t _{rr2}	T _J = 125 °C		-	106	160			
Peak recovery current	I _{RRM1}	T _J = 25 °C	I _F = 8.0 A dI _F /dt = 200 A/μs V _B = 200 V	-	4.5	8.0	A		
See fig. 6	I _{RRM2}	T _J = 125 °C		-	6.2	11			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	140	380			
See fig. 7	Q _{rr2}	T _J = 125 °C	$v_{\rm R} = 200 v$	-	335	880	nC		
Peak rate of recovery	dl _{(rec)M} /dt1	T _J = 25 °C		-	133	-			
current during t _b See fig. 8	dl _{(rec)M} /dt2	T _J = 125 °C]	-	85	-	A∕µs		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R _{thJC}		-	-	1.7				
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	K/W			
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.25	-				
Waight			-	6.0	-	g			
Weight			-	0.21	-	oz.			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)			
Marking device		Case style TO-247AC modified (JEDEC)		HFA08	PB120	-			

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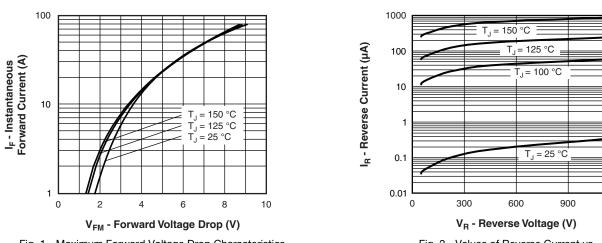
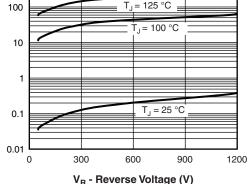
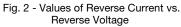


Fig. 1 - Maximum Forward Voltage Drop Characteristics





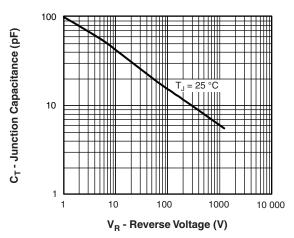
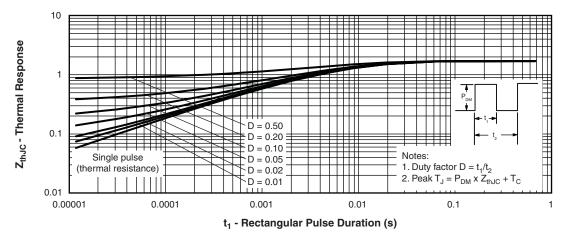


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





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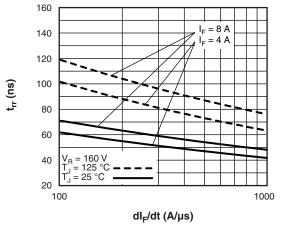


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

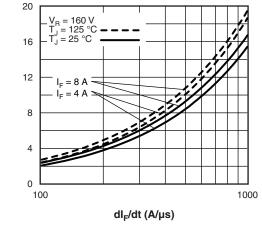
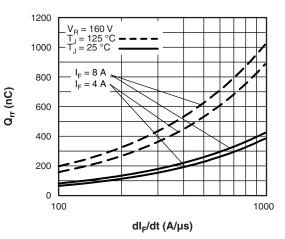


Fig. 6 - Typical Recovery Current vs. dl_F/dt



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Fig. 7 - Typical Stored Charge vs. dI_F/dt

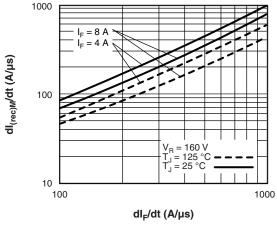


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

I_{rr} (A)

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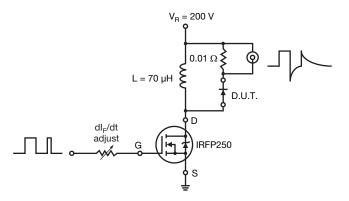


Fig. 9 - Reverse Recovery Parameter Test Circuit

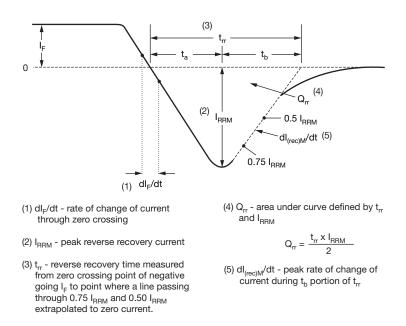


Fig. 10 - Reverse Recovery Waveform and Definitions

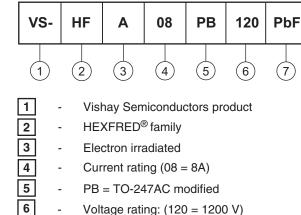
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ORDERING INFORMATION TABLE

Device code



- Voltage rating: (120 = 1200 V) _
- PbF = Lead (Pb)-free

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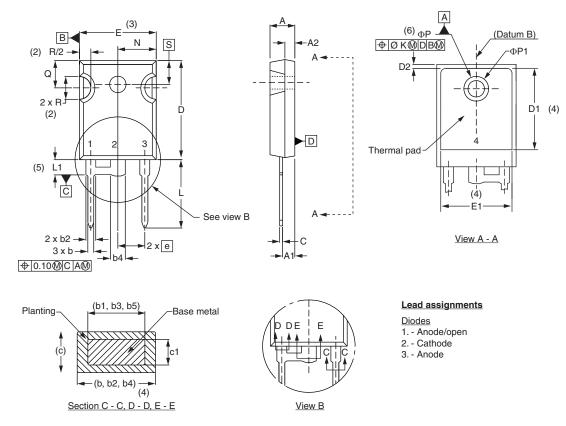
LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95253						
Part marking information	www.vishay.com/doc?95255						

Outline Dimensions





DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	IETERS	INC	HES	NOTES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STINDOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209			D2	0.51	1.30	0.020	0.051	
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3
A2	1.50	2.49	0.059	0.098			E1	13.72	-	0.540	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053			ΦK	2.	54	0.0)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.37	0.065	0.094			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			N	7.62	BSC	0.3		
b5	2.59	3.38	0.102	0.133			ΦР	3.56	3.66	0.14	0.144	
С	0.38	0.86	0.015	0.034			Φ P1	-	6.98	-	0.275	
c1	0.38	0.76	0.015	0.030			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	1.78	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	BSC	

Notes

⁽¹⁾ Dimensioning and tolerance per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

- ⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1
- ⁽⁵⁾ Lead finish uncontrolled in L1

(6) ΦP to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

⁽⁷⁾ Outline conforms to JEDEC outline TO-247 with exception of dimension c

Revision: 21-Jun-11

1

Document Number: 95253

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